

said memory cell section including, in addition to said transfer gates, said contact plugs, and said first and second interlayer insulating films,

a bit line formed on said second interlayer insulating film;

A1 a third interlayer insulating film formed on said second interlayer insulating film so as to cover said bit line; and

capacitors formed on said third interlayer insulating film;

said memory cell section further including said diameter-reduced contact plugs, which include

a bit line contact plug which extends through said second interlayer insulating film to bring said contact plugs and said bit line into conduction; and

a capacitor contact plugs which extend through said second and third interlayer insulating films to bring said contact plugs and said capacitors into conduction.

A2 5. (Amended) The semiconductor device according to claim 2, further including a logic circuit section including a plurality of transistors, said logic section including, in addition to said transfer gates, said contact plugs, and said first and second interlayer insulating films,

Sub C1 bit lines formed on said second interlayer insulating film; and

said logic circuit section further including, as said diameter-reduced contact plugs,

bit line contact plugs which extend through said second interlayer insulating film to bring said contact plugs and said bit lines into conduction.

Sub B3

A3

9. (Amended) The semiconductor device according to claim 1, further including a logic circuit section including a plurality of transistors, said logic section including, in addition to said transfer gates, said contact plugs, and said first and second interlayer insulating films, bit lines formed on said second interlayer insulating film; and said logic circuit section further including, as said diameter-reduced contact plugs, bit line contact plugs which extend through said second interlayer insulating film to bring said contact plugs and said bit lines into conduction.

REMARKS

At the time of the Office Action dated February 14, 2002, claims 1-20 were pending in this application. Of those claims, claims 1-15 have been rejected and claims 16-20 have been withdrawn from consideration pursuant to the provisions of 37 C.F.R. § 1.142(b). Claims 2, 5, and 9 have been amended. Applicant submits that the present Amendment does not generate any new matter issue.

In the second enumerated paragraph of the statement of the rejection, the Examiner asserted that the title of the invention was not descriptive. In response, the Title has been changed to --SEMICONDUCTOR DEVICE WITH TRANSFER GATE HAVING GATE INSULATING FILM AND GATE ELECTRODE LAYER--.